

Silicon NPN Power Transistors

2SC2209

DESCRIPTION

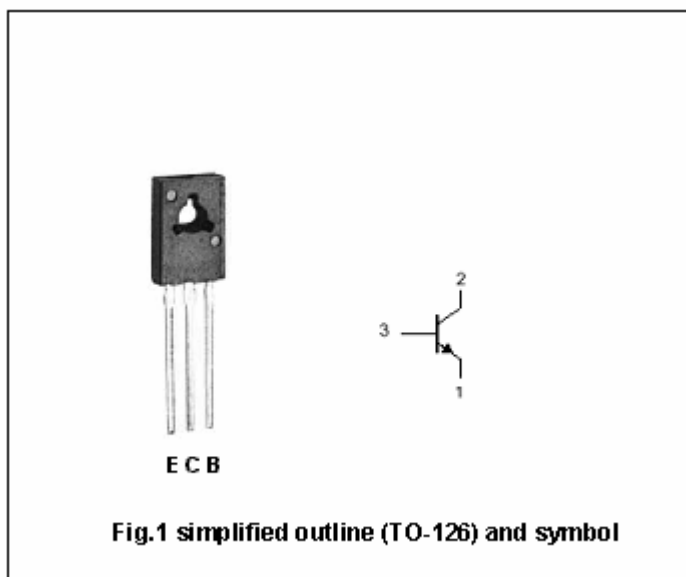
- With TO-126 package
- Complement to type 2SA963
- High collector power dissipation

APPLICATIONS

- For low-frequency power amplification

PINNING

PIN	DESCRIPTION
1	Emitter
2	Collector;connected to mounting base
3	Base



Absolute Maximun Ratings (Ta=25)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	50	V
V_{CEO}	Collector-emitter voltage	Open base	40	V
V_{EBO}	Emitter-base voltage	Open collector	5	V
I_C	Collector current (DC)		1.5	A
I_{CM}	Collector current-peak		3	A
P_C	Collector power dissipation	$T_C=25$	10	W
T_j	Junction temperature		150	
T_{stg}	Storage temperature		-55~150	

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CHARACTERISTICS

Tj=25 unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	$I_C=2mA; I_B=0$	40			V
$V_{(BR)CBO}$	Collector-base breakdown voltage	$I_C=1mA; I_E=0$	50			V
V_{CEsat}	Collector-emitter saturation voltage	$I_C=1.5A; I_B=150mA$			1.0	V
V_{BEsat}	Base-emitter saturation voltage	$I_C=2A; I_B=0.2A$			1.5	V
I_{CBO}	Collector cut-off current	$V_{CB}=20V; I_E=0$			1	μA
I_{CEO}	Collector cut-off current	$V_{CE}=10V; I_B=0$			100	μA
I_{EBO}	Emitter cut-off current	$V_{EB}=5V; I_C=0$			10	μA
h_{FE}	DC current gain	$I_C=1A; V_{CE}=5V$	80		220	
C_{OB}	Output capacitance	$I_E=0; V_{CB}=5V; f=1MHz$		50		pF
f_T	Transition frequency	$I_C=0.5A; V_{CB}=5V; f=200MHz$		150		MHz

◆ h_{FE} Classifications

Q	R
80-160	120-220

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PACKAGE OUTLINE

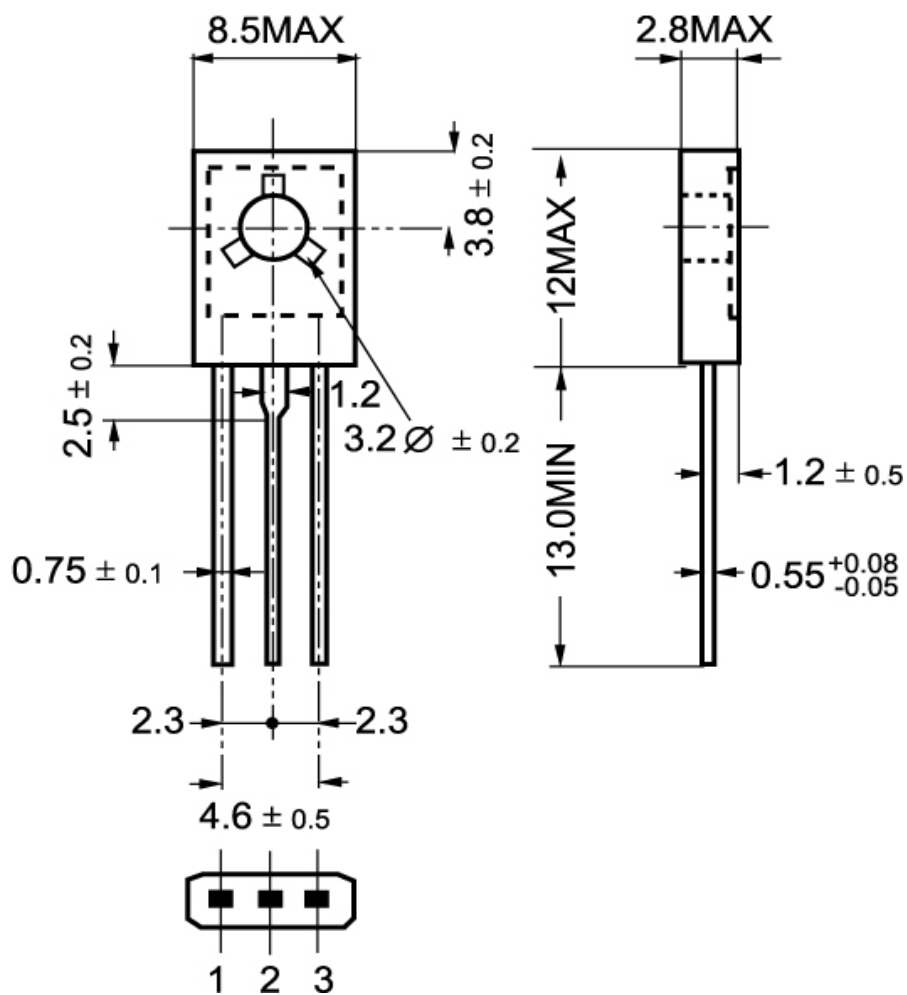


Fig.2 Outline dimensions

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